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January 2016



# **FQP3P50**

# **P-Channel QFET® MOSFET**

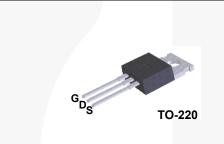
-500 V, -2.7 A, 4.9 Ω

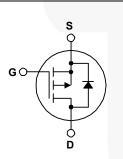
## Description

This P-Channel enhancement mode power MOSFET is • -2.7 A, -500 V,  $R_{DS(on)}$  = 4.9  $\Omega$  (Max.) @ V<sub>GS</sub> = -10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 18 nC) resistance, and to provide superior switching performance • Low Crss (Typ 9.5 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications.

## Features

- I<sub>D</sub> = -1.35 A





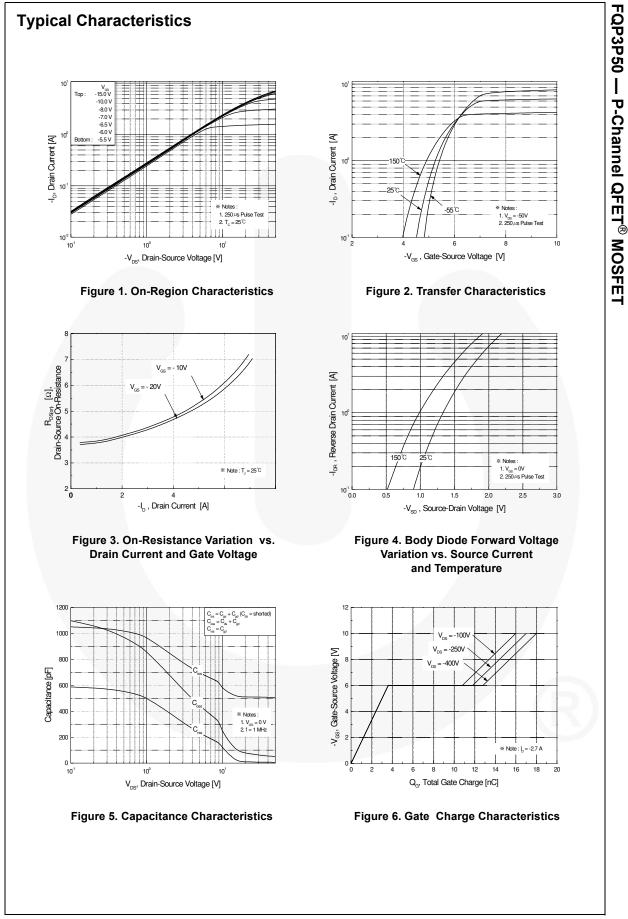
### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

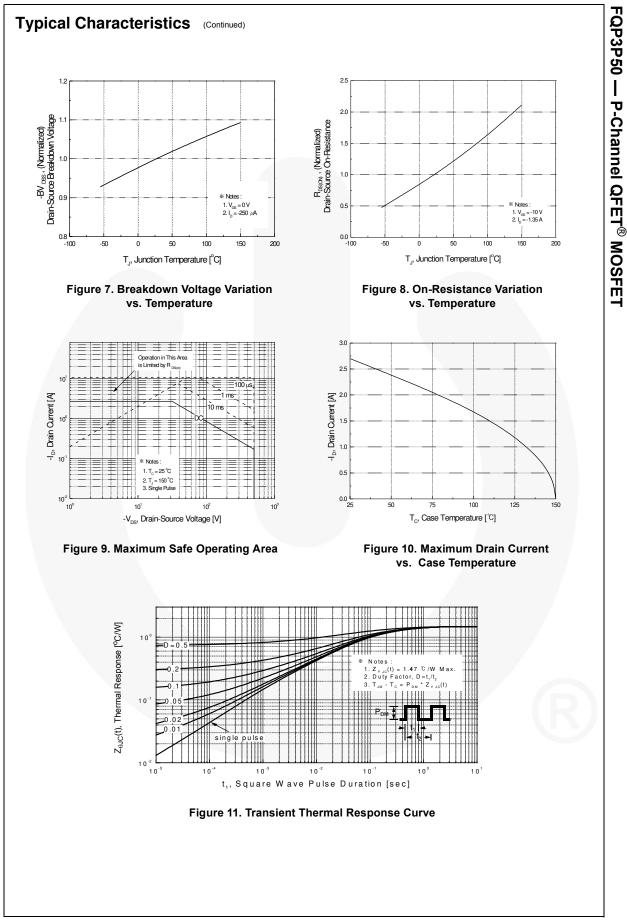
Symbol	Parameter	FQP3P50	Unit
V <sub>DSS</sub>	Drain-Source Voltage	-500	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)	-2.7	А
	- Continuous (T <sub>C</sub> = 100°C)	-1.71	A
I <sub>DM</sub>	Drain Current - Pulsed (Note	e 1) -10.8	A
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note	e 2) 250	mJ
I <sub>AR</sub>	Avalanche Current (Note	e 1) -2.7	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note	e 1) 8.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note	e 3) -4.5	V/ns
PD	Power Dissipation ( $T_C = 25^{\circ}C$ )	85	W
	- Derate above 25°C	0.68	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
Τ <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds	300	°C

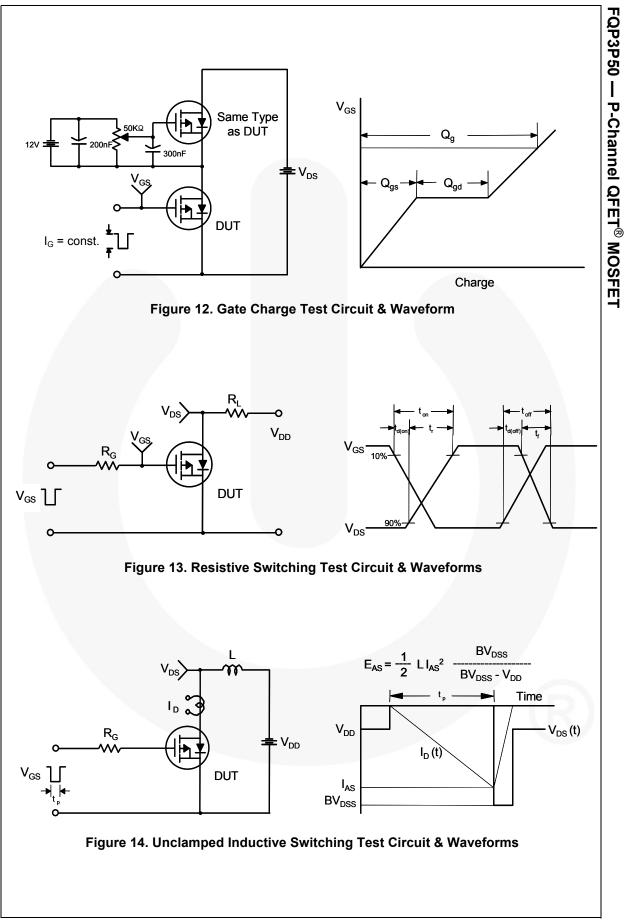
## **Thermal Characteristics**

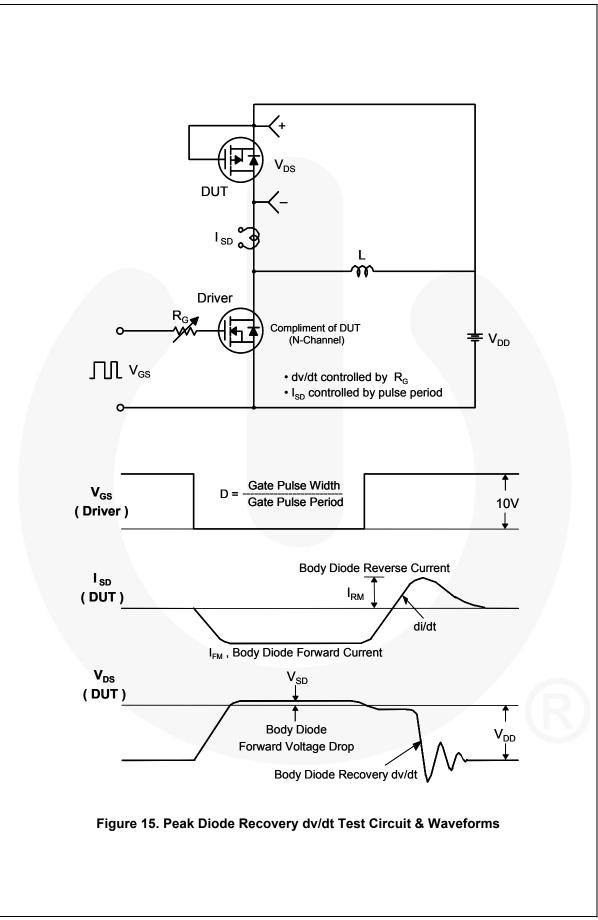
Symbol	Parameter	FQP3P50	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.47	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

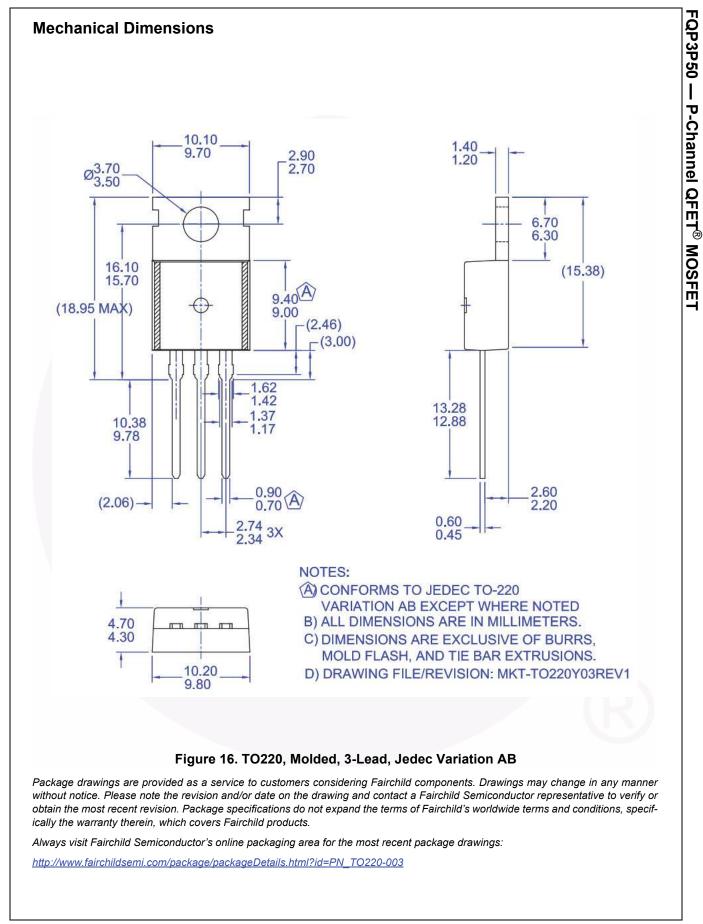
3P50 FQP3 Characteristi Parame racteristics Drain-Source Breakc	CS	TO-2							Quantity	
Paramo racteristics Drain-Source Breako			20 Tube N/A		۱	N/A	50	50 units		
Paramo racteristics Drain-Source Breako		T <sub>C</sub> = 25°C un	less other	wise noted						
Drain-Source Breako				Test Conditions		Min.	Тур.	Max.	Unit	
Drain-Source Breako					I					
		togo	Vee	= 0 V, I <sub>D</sub> = -250 μA		-500			V	
Breakdown Voltage 1		•			-500			v		
Coefficient	<b>o</b> 1		$I_D = -250 \ \mu$ A, Referenced to 25°C				0.42		V/°C	
DSS Zero Gate Voltage Drain Current GSSF Gate-Body Leakage Current, Forward		-	= -500 V, V <sub>GS</sub> = 0 V				-1	μA		
			$V_{DS} = -400 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$				-10	μA		
, ,								nA		
Gate-Body Leakage Current, Reverse		Reverse	V <sub>GS</sub> :	$= 30 \text{ V}, \text{ V}_{\text{DS}} = 0 \text{ V}$				100	nA	
racteristics						1				
Gate Threshold Volta	ige		V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = -250 μA		-3.0		-5.0	V	
Static Drain-Source On-Resistance			V <sub>GS</sub> = -10 V, I <sub>D</sub> = -1.35 A			3.9	4.9	Ω		
Forward Transcondu	ctance		V <sub>DS</sub> =	= -50 V, I <sub>D</sub> = -1.35 A			2.35		S	
	5		1							
	apacitance				-	_			pF pF	
· · ·			f = 1.0 MHz			70	90	nE		
neverse fransier Ga					F		0.5	10		
		e					9.5	12	pF	
ng Characteristic		e							pF	
Turn-On Delay Time		же 	V <sub>DD</sub> :	= -250 V, I <sub>D</sub> = -2.7 A,			12	35	pF	
Turn-On Delay Time Turn-On Rise Time		;e	00	= -250 V, I <sub>D</sub> = -2.7 A, 25 Ω			12 56	35 120	pF ns ns	
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time		;e	00		(Note 4)		12 56 35	35 120 80	pF ns ns ns	
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time		;e	R <sub>G</sub> =	25 Ω	(Note 4)		12 56 35 45	35 120 80 100	pF ns ns ns ns	
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge			R <sub>G</sub> =	25 Ω = -400 V, I <sub>D</sub> = -2.7 A,	(Note 4)		12 56 35 45 18	35 120 80 100 23	pF ns ns ns ns nC	
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge		;e	R <sub>G</sub> =	25 Ω	(Note 4)		12 56 35 45 18 3.6	35 120 80 100 23 	pF ns ns ns ns nC nC	
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge	SS		$R_{G} =$ $V_{DS} =$ $V_{GS} =$	25 Ω = -400 V, I <sub>D</sub> = -2.7 A, = -10 V			12 56 35 45 18	35 120 80 100 23	pF ns ns ns ns nC	
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge	racter	istics a	R <sub>G</sub> =	25 Ω = -400 V, I <sub>D</sub> = -2.7 A, = -10 V		      	12 56 35 45 18 3.6 9.2	35 120 80 100 23  	pF ns ns ns nC nC nC	
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Ource Diode Cha Maximum Continuou	racter	istics an Source Dic	V <sub>DS</sub> = V <sub>GS</sub> =	25 Ω = -400 V, I <sub>D</sub> = -2.7 A, = -10 V <b>Eximum Ratings</b> ward Current		      	12 56 35 45 18 3.6 9.2	35 120 80 100 23   	pF ns ns ns nC nC nC	
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Ource Diode Cha Maximum Continuou Maximum Pulsed Dra	racter s Drain- ain-Sour	istics al Source Did ce Diode F	V <sub>DS</sub> = V <sub>GS</sub> = V <sub>GS</sub> =	25 Ω = -400 V, I <sub>D</sub> = -2.7 A, = -10 V <b>Eximum Ratings</b> ward Current I Current		      	12 56 35 45 18 3.6 9.2	35 120 80 100 23      -2.7 -10.8	pF ns ns ns nC nC nC A A	
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Ource Diode Cha Maximum Continuou	racter s Drain- ain-Sour Forward	istics al Source Did ce Diode F	$R_{G} =$ $V_{DS} =$ $V_{GS} =$ <b>nd Ma</b> bde For Forward	25 Ω = -400 V, I <sub>D</sub> = -2.7 A, = -10 V <b>Eximum Ratings</b> ward Current		      	12 56 35 45 18 3.6 9.2	35 120 80 100 23   	pF ns ns ns nC nC nC	
	Gate-Body Leakage racteristics Gate Threshold Volta Static Drain-Source On-Resistance Forward Transcondu	Gate-Body Leakage Current, racteristics Gate Threshold Voltage Static Drain-Source On-Resistance Forward Transconductance c Characteristics Input Capacitance Output Capacitance	racteristics Gate Threshold Voltage Static Drain-Source On-Resistance Forward Transconductance c Characteristics Input Capacitance Output Capacitance	Gate-Body Leakage Current, Forward       V <sub>GS</sub> =         Gate-Body Leakage Current, Reverse       V <sub>GS</sub> =         racteristics       V <sub>DS</sub> =         Gate Threshold Voltage       V <sub>DS</sub> =         Static Drain-Source       V <sub>GS</sub> =         On-Resistance       V <sub>DS</sub> =         Forward Transconductance       V <sub>DS</sub> =         C Characteristics       Input Capacitance         VDS =       V <sub>DS</sub> =	Gate-Body Leakage Current, Forward $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$ racteristics $V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = -250 \mu \text{A}$ Static Drain-Source $V_{GS} = -10 \text{ V}, I_D = -1.35 \text{ A}$ On-Resistance $V_{DS} = -50 \text{ V}, I_D = -1.35 \text{ A}$ Forward Transconductance $V_{DS} = -50 \text{ V}, I_D = -1.35 \text{ A}$ Input Capacitance $V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$	Gate-Body Leakage Current, Forward $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$ racteristicsGate Threshold Voltage $V_{DS} = V_{GS}, I_D = -250 \mu \text{A}$ Static Drain-Source $V_{GS} = -10 \text{ V}, I_D = -1.35 \text{ A}$ On-Resistance $V_{DS} = -50 \text{ V}, I_D = -1.35 \text{ A}$ Forward Transconductance $V_{DS} = -50 \text{ V}, I_D = -1.35 \text{ A}$ c CharacteristicsInput Capacitance $V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$	Gate-Body Leakage Current, Forward $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$ racteristicsGate Threshold Voltage $V_{DS} = V_{GS}, I_D = -250 \mu \text{ A}$ -3.0Static Drain-Source $V_{GS} = -10 \text{ V}, I_D = -1.35 \text{ A}$ On-Resistance $V_{DS} = -50 \text{ V}, I_D = -1.35 \text{ A}$ Forward Transconductance $V_{DS} = -50 \text{ V}, I_D = -1.35 \text{ A}$ C CharacteristicsInput Capacitance $V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$	Gate-Body Leakage Current, Forward $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$ racteristicsGate Threshold Voltage $V_{DS} = V_{GS}, I_D = -250 \mu \text{ A}$ -3.0Static Drain-Source $V_{GS} = -10 \text{ V}, I_D = -1.35 \text{ A}$ 3.9On-Resistance $V_{DS} = -50 \text{ V}, I_D = -1.35 \text{ A}$ 2.35Forward Transconductance $V_{DS} = -50 \text{ V}, I_D = -1.35 \text{ A}$ 510Input Capacitance $V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$ 510	Gate-Body Leakage Current, Forward $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ 100Gate-Body Leakage Current, Reverse $V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$ 100racteristicsGate Threshold Voltage $V_{DS} = V_{GS}, I_D = -250 \mu \text{ A}$ -3.05.0Static Drain-Source $V_{GS} = -10 \text{ V}, I_D = -1.35 \text{ A}$ 3.94.9On-Resistance $V_{DS} = -50 \text{ V}, I_D = -1.35 \text{ A}$ 2.35c CharacteristicsInput Capacitance $V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$ 510660	











<sup>=</sup>QP3P50 — P-Channel QFET<sup>®</sup> MOSFE<sup>-</sup>



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